



Trench IGBT Modules

SEMiX302GB12E4s

Features

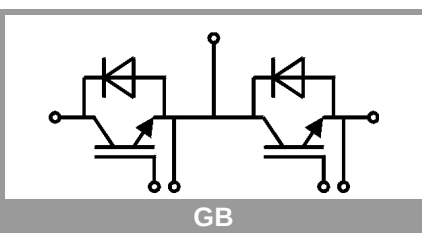
- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability
- UL recognized, file no. E63532

Typical Applications*

- AC inverter drives
- UPS
- Electronic Welding

Remarks

- Case temperature limited to $T_C=125^\circ\text{C}$ max.
- Product reliability results are valid for $T_J=150^\circ\text{C}$
- Dynamic values apply to the following combination of resistors:
 $R_{Gon,main} = 0,5 \Omega$
 $R_{Goff,main} = 0,5 \Omega$
 $R_{G,X} = 2,2 \Omega$
 $R_{E,X} = 0,5 \Omega$



Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
IGBT				
V _{CES}			1200	V
I _C	T _j = 175 °C	T _c = 25 °C	463	A
		T _c = 80 °C	356	A
I _{Cnom}			300	A
I _{CRM}	I _{CRM} = 3xI _{Cnom}		900	A
V _{GES}			-20 ... 20	V
t _{psc}	V _{CC} = 800 V V _{GE} ≤ 20 V V _{CES} ≤ 1200 V	T _j = 150 °C	10	µs
T _j			-40 ... 175	°C
Inverse diode				
I _F	T _j = 175 °C	T _c = 25 °C	356	A
		T _c = 80 °C	266	A
I _{Fnom}			300	A
I _{FRM}	I _{FRM} = 3xI _{Fnom}		900	A
I _{FSM}	t _p = 10 ms, sin 180°, T _j = 25 °C		1620	A
T _j			-40 ... 175	°C
Module				
I _{t(RMS)}			600	A
T _{stg}			-40 ... 125	°C
V _{isol}	AC sinus 50Hz, t = 1 min		4000	V

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
IGBT						
V _{CE(sat)}	I _C = 300 A	T _J = 25 °C		1.8	2.05	V
	V _{GE} = 15 V chipelevel	T _J = 150 °C		2.2	2.4	V
V _{CE0}		T _J = 25 °C		0.8	0.9	V
		T _J = 150 °C		0.7	0.8	V
r _{CE}	V _{GE} = 15 V	T _J = 25 °C		3.3	3.8	mΩ
		T _J = 150 °C		5.0	5.3	mΩ
V _{GE(th)}	V _{GE} =V _{CE} , I _C = 12 mA		5	5.8	6.5	V
I _{CES}	V _{GE} = 0 V	T _J = 25 °C		0.1	0.3	mA
	V _{CE} = 1200 V	T _J = 150 °C				mA
C _{ies}	V _{CE} = 25 V	f = 1 MHz		18.6		nF
C _{oes}	V _{GE} = 0 V	f = 1 MHz		1.16		nF
C _{res}		f = 1 MHz		1.02		nF
Q _G	V _{GE} = - 8 V...+ 15 V			1700		nC
R _{Gint}	T _J = 25 °C			2.50		Ω
t _{d(on)}	V _{CC} = 600 V	T _J = 150 °C		282		ns
t _r	I _C = 300 A	T _J = 150 °C		60		ns
E _{on}	R _{G on} = 1.9 Ω	T _J = 150 °C		30		mJ
t _{d(off)}	R _{G off} = 1.9 Ω	T _J = 150 °C		564		ns
t _f	di/dt _{on} = 5000 A/μs	T _J = 150 °C		117		ns
E _{off}	di/dt _{off} = 2800 A/μs	T _J = 150 °C		44		mJ
R _{th(j-c)}	per IGBT				0.096	K/W



SEMiX® 2s

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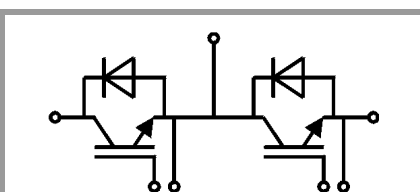
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Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverse diode						
V _F = V _{EC}	I _F = 300 A	T _j = 25 °C		2.1	2.46	V
	V _{GE} = 0 V chip	T _j = 150 °C		2.1	2.4	V
V _{F0}		T _j = 25 °C	1.1	1.3	1.5	V
		T _j = 150 °C	0.7	0.9	1.1	V
r _F		T _j = 25 °C	2.2	2.8	3.2	mΩ
		T _j = 150 °C	3.3	3.9	4.3	mΩ
I _{RRM}	I _F = 300 A	T _j = 150 °C	230			A
Q _{rr}	di/dt _{off} = 4300 A/μs	T _j = 150 °C	50			μC
E _{rr}	V _{GE} = -15 V V _{CC} = 600 V	T _j = 150 °C	19			mJ
R _{th(j-c)}	per diode		0.17			K/W
Module						
L _{CE}			18			nH
R _{CC'+EE'}	res., terminal-chip	T _C = 25 °C	0.7			mΩ
		T _C = 125 °C	1			mΩ
R _{th(c-s)}	per module		0.045			K/W
M _s	to heat sink (M5)		3	5		Nm
M _t		to terminals (M6)	2.5	5		Nm
						Nm
w			250			g
Temperatur Sensor						
R ₁₀₀	T _c =100°C (R ₂₅ =5 kΩ)		493 ± 5%			Ω
B _{100/125}	R _(T) =R ₁₀₀ exp[B _{100/125} (1/T-1/T ₁₀₀)]; T[K];		3550 ±2%			K



GB

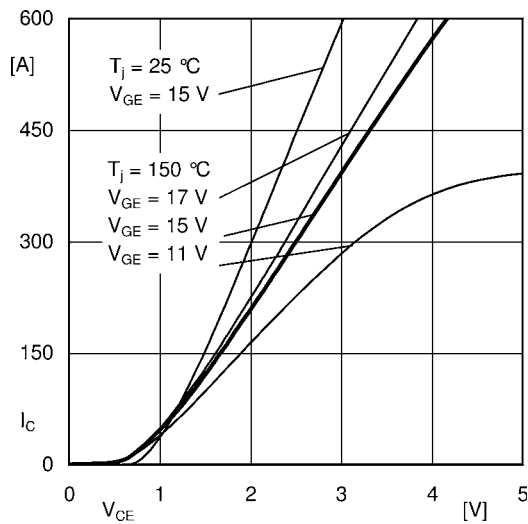
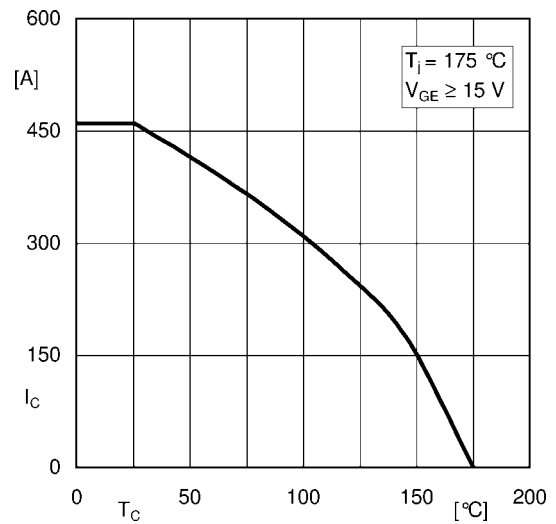
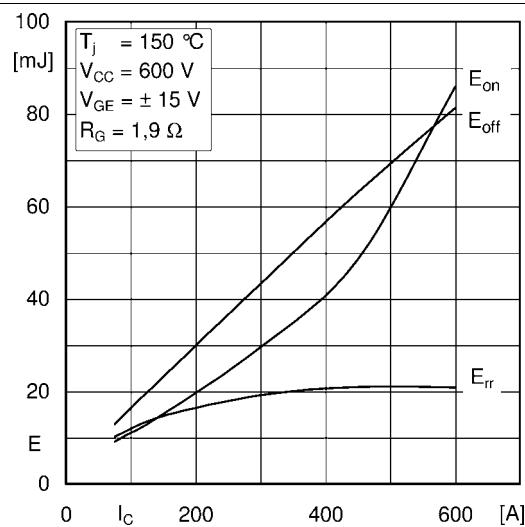
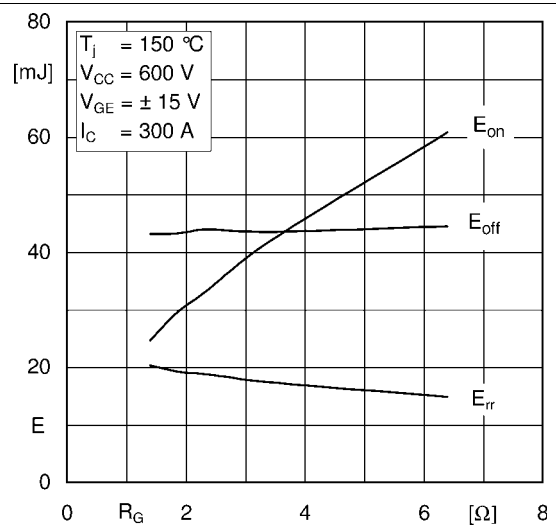
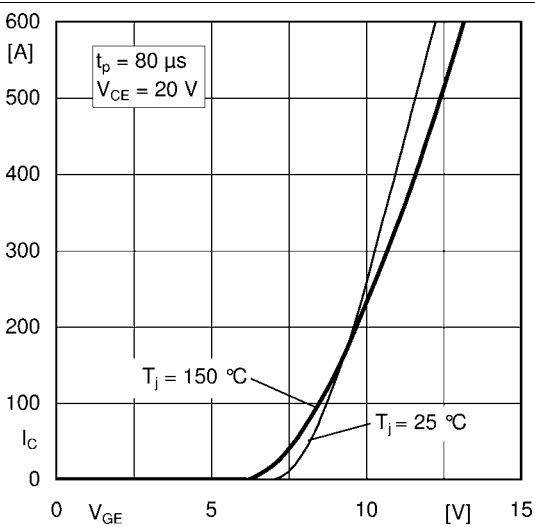
Fig. 1: Typ. output characteristic, inclusive $R_{CC} + EE'$ Fig. 2: Rated current vs. temperature $I_C = f(T_C)$ Fig. 3: Typ. turn-on /-off energy = $f(I_C)$ Fig. 4: Typ. turn-on /-off energy = $f(R_G)$ 

Fig. 5: Typ. transfer characteristic

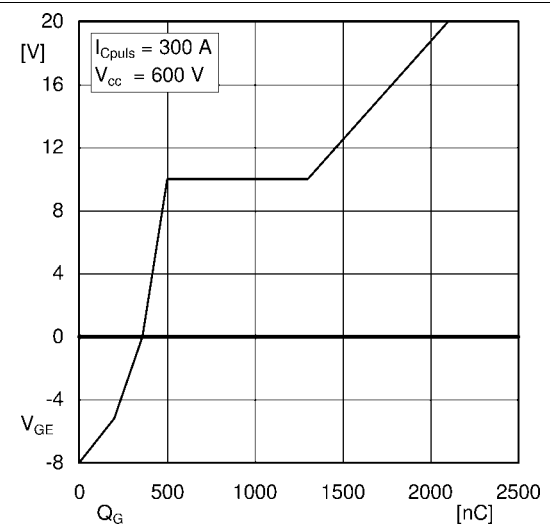


Fig. 6: Typ. gate charge characteristic

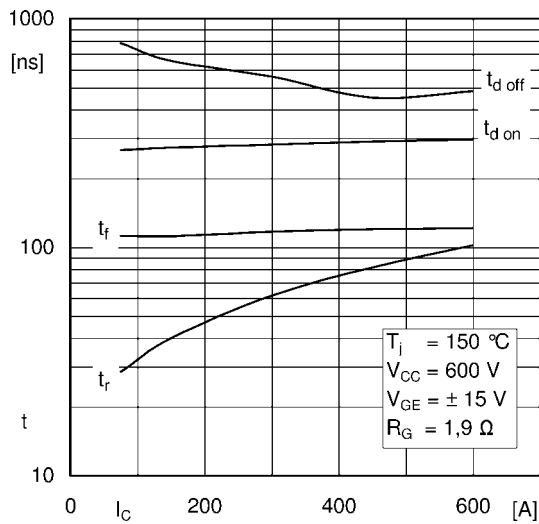
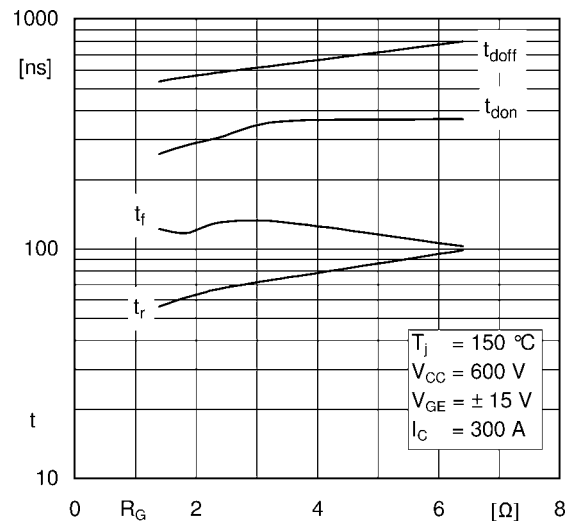
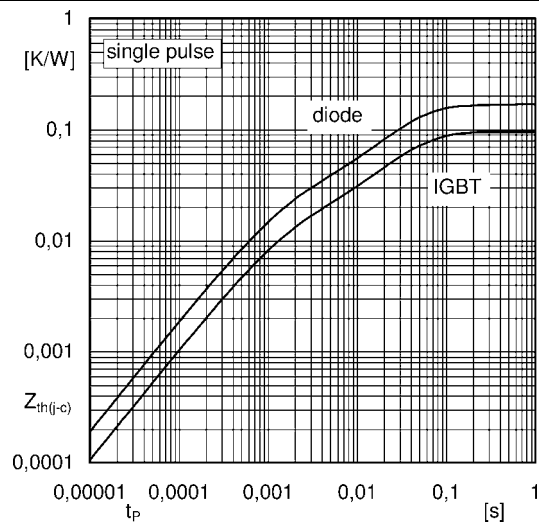
Fig. 7: Typ. switching times vs. I_C Fig. 8: Typ. switching times vs. gate resistor R_G 

Fig. 9: Typ. transient thermal impedance

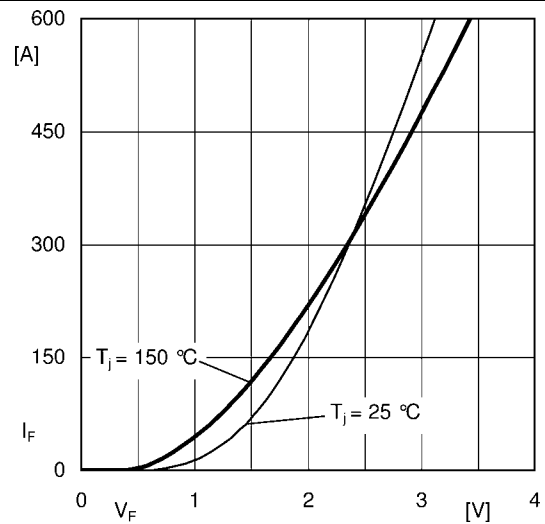
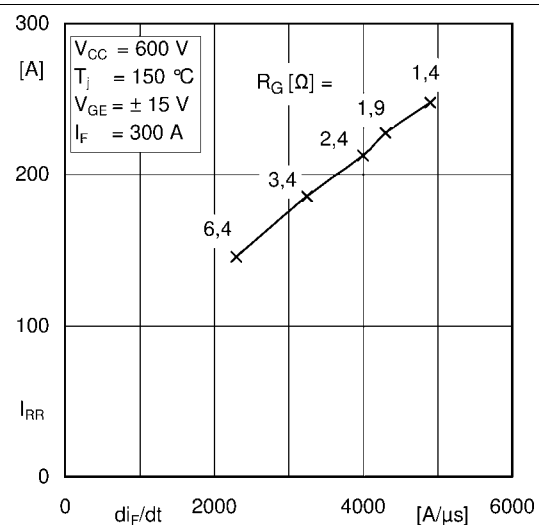
Fig. 10: Typ. CAL diode forward charact., incl. $R_{CC'+EE'}$ 

Fig. 11: Typ. CAL diode peak reverse recovery current

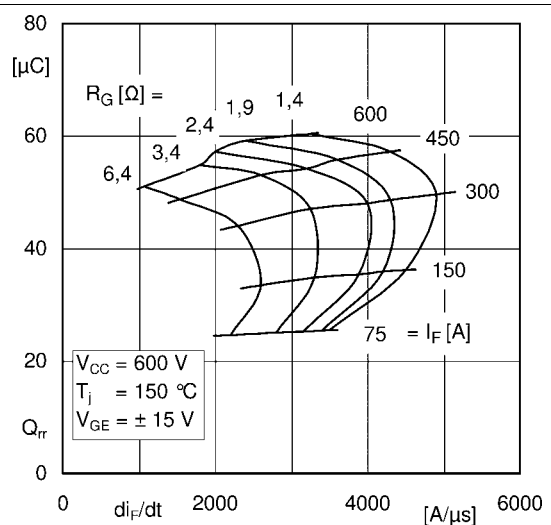
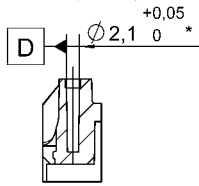
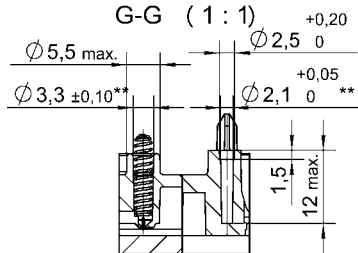
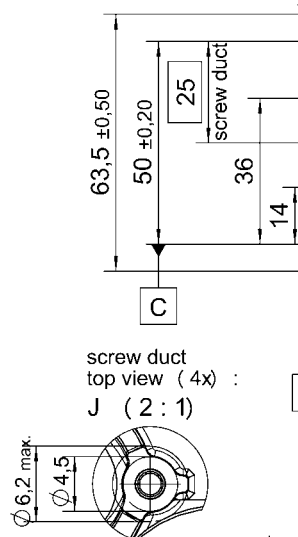
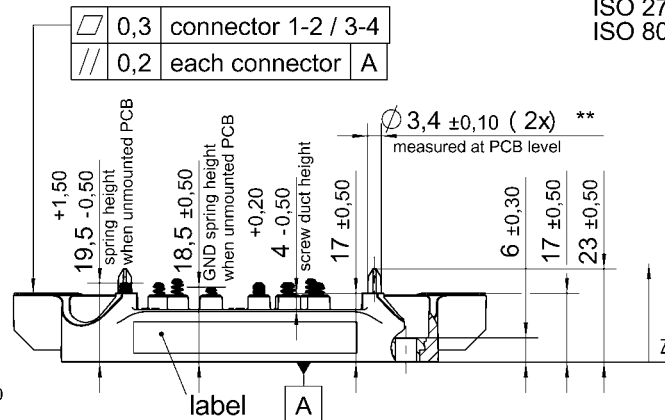
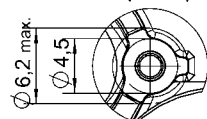


Fig. 12: Typ. CAL diode recovery charge

Case: SEMiX 2s

screw duct
(left top) :
F-F (1:1)screw duct (4x)
spring duct (12x) :
G-G (1:1)

marking of terminals

screw duct
top view (4x) :
J (2:1)

0,3	connector 1-2 / 3-4
0,2	each connector A

general tolerance:
ISO 2768-mK
ISO 8015All measures in Z-direction
valid when mounted to heat sink

0	screw ducts / guide pin
0,05	
0,3	
8,4	
12,9	
21,25	
33,05	
39,85	
40,55	
45,9	
47,75	
61,5	screw ducts / guide pin

marking of terminals

0	screw ducts
8,1	
8,55	
15	guide pin
21,55	
25	guide pin
26,05	
41,95	
45,5	
46,05	
50	screw ducts

M6 -10 deep

*screw duct left / top with

⌀	⌀ 0,2	A	B	C
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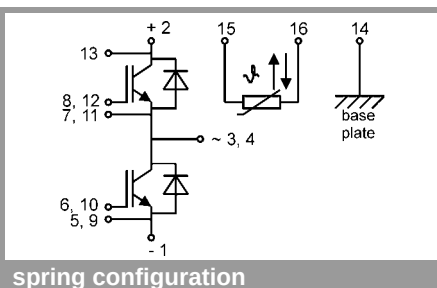
**screw ducts / guide pins / spring ducts with

⌀	⌀ 0,2	A	D	C
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Rules for the contact PCB:

- holes guidepins = $\varnothing 4 \pm 0,1$ / position tolerance $\pm 0,1$
- holes for screws = $\varnothing 2,9 \pm 0,1$ / position tolerance $\pm 0,1$
- spring contact pad = $\varnothing 3,6 \pm 0,1$ / position tolerance $\pm 0,1$

SEMiX 2s



spring configuration

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.